How strong is the Second Harmonic Generation in single-layer monochalcogenides? 
A response from first-principles real-time simulations
Claudio Attaccalite,1,2 Maurizia Palummo,3,2 Elena Cannuccia,3,4 and Myrta Grüning5,2
1 CNRS/Aix-Marseille Université, Centre Interdisciplinaire de Nanoscience de Marseille UMR 7325 Campus de Luminy, 13288 Marseille Cedex 9, France
2 European Theoretical Spectroscopy Facilities (ETSF)
3 University of Rome Tor Vergata, Rome, Italy
4 Université Aix-Marseille, Laboratoire de Physique des Interactions Ioniques et Moléculaires (PIHM), UMR CNRS 7345, F-13397 Marseille, France
5 School of Mathematics and Physics, Queen’s University Belfast, Belfast BT7 1NN, Northern Ireland, UK

Second Harmonic Generation (SHG) of single-layer monochalcogenides, such as GaSe and InSe, has been recently reported [2D Mater. 5 (2018) 025019; J. Am. Chem. Soc. 2015, 137, 7994–7997] to be extremely strong with respect to bulk and multilayer forms. To clarify the origin of this strong SHG signal, we perform first-principles real-time simulations of linear and non-linear optical properties of these two-dimensional semiconducting materials. The simulations, based on ab-initio many-body theory, accurately treat the electron-hole correlation and capture excitonic effects that are deemed important to correctly predict the optical properties of such systems. We find indeed that, as observed for other 2D systems, the SHG intensity is redistributed at excitonic resonances. The obtained theoretical SHG intensity is an order of magnitude smaller than that reported at the experimental level. This result is in substantial agreement with previously published simulations which neglected the electron-hole correlation, demonstrating that many-body interactions are not at the origin of the strong SHG measured. We then show that the experimental data can be reconciled with the theoretical prediction when a single layer model, rather than a bulk one, is used to extract the SHG coefficient from the experimental data.

I. INTRODUCTION

Nowadays there is a considerable interest in the excited state properties of 2D materials which can be distinctly different from that of their bulk counterpart.1–4 Strongly bound excitons often characterize the optical spectra of two-dimensional (2D) semiconducting crystals and in several cases, intense nonlinear optical spectra have been observed4–8 such as strong second-harmonic generation (SHG)—typically up to one order of magnitude larger than in conventional non-linear crystals. For this reason these materials are of potential technological interest as frequency converters in nanophotonic circuits.9 Furthermore, the SHG is an excellent spectroscopic tool for the imaging and characterization of 2D materials,10–12 and understand the origin of the signal from theoretical point of view is of fundamental importance for the interpretation.

Recently, extremely large values have been reported for SHG of single-layer monochalcogenides: for InSe13 a value of 6.39 nm/V at 1.55 eV and for GaSe14 a value of 2.4 nm/V at 1.02 eV. To put these values into perspective, the SHG of single-layer MoS2 is of the order of 0.1–0.4 nm/V15 at resonance, that of bi- and tri- and multilayer15–17 GaSe ranges from 9–90 pm/V, and that of bulk GaSe is about 60 pm/V. A similar large SHG of 10 nm/V was reported for WS2 and WSe2 monolayers.18 However, the extremely large SHG coefficients for single-layer monochalcogenides are not confirmed by first-principle calculations,19–21 which give consistently values smaller by one order of magnitude.

The discrepancy between the theoretical and experimental results may be due to many-body effects that were neglected in the computational studies of Refs. 18 and 19. In fact, electron-electron interaction and excitonic effects are known to play a crucial role in the description of optical properties, especially in the case of low-dimensional materials. Indeed the incomplete screening of the electron-electron interaction and the quantum confinement may further enhance these effects with respect to bulk. Specifically for single-layer monochalcogenides, the formation of strong bound excitons have been recently shown in Ref. 20. Further, their peculiar optical properties have been attributed to saddle-points excitations22 that originate from the Mexican hat-like band structure near the Γ point.22,23

![Ball-and-stick representation of the atomic structure of the GaSe (InSe) monolayer: top view (a) and lateral view (b). Gallium (Indium) atoms are in gray, Selenium in yellow.](image)

FIG. 1. [Color online] Ball-and-stick representation of the atomic structure of the GaSe (InSe) monolayer: top view (a) and lateral view (b). Gallium (Indium) atoms are in gray, Selenium in yellow.

This work addresses the question of whether the extremely large SHG of single-layer monochalcogenides is due to strongly bound excitons. To this end, by using a first-principle real-time approach based on many-body theory (Sec. II), we calculate the electronic structure, di-
electric function (Sec. [II A] and the SHG (Sec. [II B]) of InSe and GaSe monolayers and, in order to single out many-body effects, we compare with the results at the independent-particle level. Previous studies on h-BN, MoS$_{2}$ and other semiconducting 2D materials found a significant enhancement at resonance of the SHG signal due to excitonic effects—up to 2–4 times depending on the system. For single-layer monochalcogenides, we find that intensity is only slightly redistributed by many-body effects respect to the independent-particle approximation. We conclude (Sec. [IV]) that many-body effects do not account for the difference between theoretical predictions and experimental estimates. We turn then the attention to the experimental results and argue that the extremely large SHG coefficient is an artifact of the model assumed to extract the estimate from the experimental data.

II. THEORETICAL FRAMEWORK AND COMPUTATIONAL DETAILS

The structural optimization and electronic structure have been calculated using density-functional theory (DFT). The crystal structure of the GaSe and InSe monolayers (Fig. 1) has been obtained from the corresponding bulk structure using the same in-plane lattice parameters ($a = 0.374$ nm and $a = 0.4$ nm respectively for the GaSe and the InSe monolayer) and optimizing the atomic positions. In order to simulate an isolated monolayer, we used a 35 a.u. supercell in the z-direction.

DFT calculations have been performed with the Quantum-Espresso code\textsuperscript{23} using the Perdew-Burke-Ernzerhof\textsuperscript{29} (PBE) functional and the scalar-relativistic optimized norm-conserving Vanderbilt\textsuperscript{30} pseudopotentials from the PseudoDojo repository (v0.4) \textsuperscript{23} We use a shifted 18 x 18 x 1 k-point sampling for the ground-state, a plane-wave cutoff of 90 Ry for the structural optimization and of 70 Ry for the band-structure calculations.

Calculations of the quasi-particle energies and optical susceptibilities have been performed using the Yambo code.\textsuperscript{32-34} The quasiparticle corrections to the fundamental band gap have been calculated from the standard $G_{0}W_{0}$ approximation with the Godby-Needs plasmon-pole model\textsuperscript{35} and applied as a right shift to all the bands. We used a 24 x 24 x 1 k-point sampling, a 5 Ha cutoff for the dielectric function, and 200 bands for Green’s function expansion. Convergence with the number of conduction bands was accelerated by means of the Bruneval-Gonze terminator.\textsuperscript{29} Optical absorption spectra have been obtained by the solution of the Bethe-Salpeter equation\textsuperscript{37} using a basis of electron-hole pairs for which we considered 6 valence and 5 conduction states for both GaSe and InSe monolayers.

Non-linear susceptibilities have been obtained from the real-time evolution of Bloch-electrons in a uniform time-dependent electric field following the approach proposed in Ref. \textsuperscript{24} and \textsuperscript{38}. The effective Hamiltonian for the Bloch electrons, derived from many-body theory, contains both the electron-hole attraction (through a screened-Coulomb term) and exchange (through a Hartree term) needed to describe excitons and local-field depolarization effects. The whole framework is based on DFT and quasiparticle corrections are included at the level of $G_{0}W_{0}$. In the linear-response limit, the approach is equivalent to the solution of the BSE on top of the $G_{0}W_{0}$ electronic structure\textsuperscript{39} and we therefore refer to this level of theory as $G_{0}W_{0}$+BSE for both linear and nonlinear susceptibilities. Within this framework, we can exclude specific terms from the effective Hamiltonian to investigate how they affect the SHG. In particular, we consider the independent-particle approximation (IPA)—no electron-hole correlation; the random-phase approximation (RPA)—only electron-hole exchange. Further, we perform the simulations on top of either the DFT or the $G_{0}W_{0}$ electronic structure. For the screened-Coulomb and Hartree terms, we use the same parameters as in the BSE calculations.

After the integration of the equation-of-motion, the nonlinear susceptibilities $\chi^{(n)}$ are extracted using Fourier techniques from the macroscopic polarization $P$—calculated as a dynamic Berry-phase\textsuperscript{40} and its expansion in power of the total electric field $E$:

\begin{equation}
P_{i} = \chi_{ij}^{(1)} E_{j} + \chi_{ijk}^{(2)} E_{j} E_{k} + \chi_{ijkl}^{(3)} E_{j} E_{k} E_{l} + O(E^{4}),
\end{equation}

where the $i,j,k,l$ subscripts refer to Cartesian components of the field and polarization.

Specifically, to obtain a single SHG spectrum we per-
form a series of simulations of about 75 fs for a monochromatic electric field with frequency ranging from 0.1 eV to 7.0 eV. We integrate the equation-of-motion using the Crack-Nicholson method\textsuperscript{31} with a time-step of 0.01 fs. Since the turning-on of the electric field excites all eigenfrequencies of the system, to damp them we introduce a phenomenological dephasing term corresponding to a Lorentzian broadening of the spectrum of 0.2 eV. Note that the intensity of SHG depends on this phenomenological parameter.

When the amplitude of the eigenfrequencies contributions becomes negligible (after about 33 fs), we perform the Fourier analysis as detailed in Ref. 38. The static limit ($\omega = 0$) has been obtained by extrapolation of the values at small frequencies.

The external electric field is polarized along the $y$ direction and the polarization is recorded in the same direction, obtaining the $\chi^{(2)}_{yyy} = -\chi^{(2)}_{xxy} = -\chi^{(2)}_{yxx} = -\chi^{(2)}_{zxy} = -\chi^{(2)}_{aan}$ that is the only nonzero component of the second-order susceptibility tensor for the hexagonal $D_{3h}$ crystal class\textsuperscript{22} being $a$ and $b$ the in-plane crystal axes. The susceptibilities are obtained for the supercell geometry. In order to obtain the SHG for a single layer we rescale the obtained $\chi^{(2)}$ by an effective thickness of 0.796 nm for the GaSe and 0.832 nm for the InSe—corresponding to half of $c$ lattice parameter of the bulk structures.\textsuperscript{22}

### III. RESULTS

#### A. Electronic structure and optical properties

In Fig. 2 we report the electronic band structure of both monochalcogenide monolayers and the position of the lowest excitons obtained from the solution of the BSE. Because of the mirror-plane symmetry ($z \rightarrow -z$), electronic states near the edges are either even or odd with respect to this symmetry operation.\textsuperscript{33} As a result, the lowest-energy electron-hole transition—depicted by a white arrow—is optically inactive for in-plane polarized light and only slightly coupled to $z$-polarized light.\textsuperscript{20,24}

In the same figure, we also indicate the lowest optical active transition with a black arrow.

The band structure is in good agreement with previous results obtained by Hu et al.\textsuperscript{18} while we found small differences respect to Antonius et al.\textsuperscript{20} who reported a larger energy difference between the two top valence bands at the vicinity of $\Gamma$.

In Fig. 3 (bottom panels), we report the imaginary part of the dielectric function of GaSe for in-plane polarized light. The two lowest excitons in GaSe are dark for light polarized in the plane due to the symmetry of the bands close to the $\Gamma$ point (while they have a small but nonzero dipole for light polarization in the $z$ direction). Our results are in good agreement with those of Antonius et al.\textsuperscript{20}

For the InSe monolayer (bottom panels of Fig. 4) we obtained similar results. The lowest excitation at 2.47 eV is dark for in-plane polarized light and the first bright exciton is at 2.63 eV. This is in agreement with luminescence measurements that found that the lowest-energy transition is not optically active in InSe monolayer.\textsuperscript{34}

Therefore, the lowest excitons do not contribute to the second-order susceptibility for in-plane polarized light.

#### B. Second Harmonic Generation

In Table I, we report the static $\chi^{(2)}(0)$ at different levels of theory: IPA, RPA, independent-particle on top of the $G_0W_0$ band structure, and finally the full $G_0W_0$+BSE. At the independent-particle level we found a large static second order susceptibility for both systems. The susceptibility is sensitive to the electronic structure and in particular to the band gap: a larger band gap corresponds to a smaller $\chi^{(2)}(0)$ as one can see going from DFT to the $G_0W_0$. Also, the band structure of InSe is similar to that of GaSe and the gap at DFT level is 1.82 eV against 2.34 eV of GaSe. As a consequence InSe has a larger $\chi^{(2)}(0)$.

The GaSe result at $G_0W_0$ is compatible with the result of Hu et al.\textsuperscript{18} that found a $\chi^{(2)}(0) = 69.4$ pm/V starting from a DFT band structure obtained by means of the Heyd-Scuseria-Ernzerhof hybrid functional that has a gap of 3.34 eV, in-between the PBE 2.34 eV and the $G_0W_0$ 4.03 eV band gap values. For the InSe monolayer, Lin et al.\textsuperscript{18} report a value of 91.3 pm/V, compatible with our result, considering that they assumed a smaller effective thickness. Lin et al. also investigated other possible structures of the InSe monolayer with a stronger SHG but we are not aware of experimental realization of these polymorphs and therefore we limit our analysis to the hexagonal monolayer.

Within the RPA, local field effects—that originate from charge fluctuations induced by the system inhomogeneity—attenuate the second order susceptibility in both GaSe and InSe monolayers. This reduction has been observed as well for other low-dimensional systems and in bulk.\textsuperscript{35} Within the $G_0W_0$+BSE, excitonic effects tend to increase the $\chi^{(2)}(0)$ and counteract the reduction from both local-field effects and quasiparticle

<table>
<thead>
<tr>
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<th>$\chi^{(2)}$(IPA)</th>
<th>$\chi^{(2)}$(RPA)</th>
<th>$\chi^{(2)}$(G$_0$W$_0$)</th>
<th>$\chi^{(2)}$(G$_0$W$_0$+BSE)</th>
</tr>
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<tbody>
<tr>
<td>GaSe</td>
<td>121</td>
<td>79.8</td>
<td>59.0</td>
<td>86.3</td>
</tr>
<tr>
<td>InSe</td>
<td>139</td>
<td>89.0</td>
<td>71.3</td>
<td>126</td>
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TABLE I. Static limit of the SHG, $\chi^{(2)}(\omega = 0)$, obtained from real-time simulations at different levels of approximation: independent-particles approximation (IPA) and the random-phase approximation (RPA) on top of the DFT electronic-structure, the IPA ($G_0W_0$) and the real-time BSE ($G_0W_0$+BSE) on top of the $G_0W_0$ electronic-structure. Units in pm/V.
The SHG intensity at $G_0W_0+BSE$ level is for both material similar to the IPA one. Figures 3 and 4 (a) and b)) show the imaginary, real part and absolute value of the SHG for GaSe and InSe monolayers within the IPA (a) and c)) and $G_0W_0+BSE$ (b) and d)). They are compared with the imaginary part of the dielectric function at $\omega$ and $2\omega$ (bottom panels) at the same level of theory. From the comparison, the main spectral features in the SHG are easily recognizable as two-photon resonances at the van Hove (IPA) and exciton energies ($G_0W_0+BSE$). We focus here on the features below the onset of the optical absorption (imaginary part of the dielectric function $\varepsilon_2$). For GaSe, comparing the IPA with the $G_0W_0+BSE$ results, we first notice that the transparency region is extended by 1 eV and the SHG intensity (absolute value) redistributed to higher energies. The lowest energy feature in the SHG intensity at the IPA level is a broad shoulder at about 1.3 eV. In the $G_0W_0+BSE$ instead, the lowest feature in the SHG intensity is a peak at about 1.75 eV which corresponds to a two-photon resonance with the lowest optical active excitons. Overall, the SHG absolute value is lower at the $G_0W_0+BSE$ than at the IPA level. The reduction is mainly due to the quasiparticle shift (a larger band gap corresponds to a lower SHG as discussed above) which is only partially compensated by the excitonic effects. A similar trend can be observed for InSe. The transparency region is extended by 0.4 eV and again the SHG intensity is redistributed at higher energies and enhanced at excitonic resonances.

IV. DISCUSSION AND CONCLUSIONS

The first thing to observe is that the inclusion of many-body effects changes the SHG spectrum: both at the level of the electronic structure (quasiparticle corrections within the $G_0W_0$) and at the level of the response function (inclusion of excitonic effects). Then, many-body effects may be important when considering technological applications.
FIG. 4. [Color online] SHG [a) and b)] and optical absorption [c) and d)] of InSe monolayer for in-plane light polarization calculated at the independent-particle [a) and c)] and at the $G_0W_0$ + Bethe-Salpeter Equation level of approximation [b) and d)]. In a) and b) we plot the real part (blue line), imaginary part (red line) and the absolute value (overshadow area) of the SHG, $\chi^{(2)}(\omega)$. In c) and d) we plot the imaginary part of the dielectric function calculated at $\omega$ (continuous line) and at $\omega/2$ (dashed line). In d) we also report the position of the two lowest bright (continuous black vertical line) and two lowest dark (dashed black vertical line) exciton energies for in-plane light polarization.

On the other hand, the theoretically predicted intensities—both with and without the inclusion of many-body effects—differ substantially from the experimental values. For GaSe, Ref. 8 reports 0.7 nm/V at 0.77 eV, 1.7 nm/V at 0.92 eV and 2.4 nm/V at 1.02 eV whereas we find 0.1, 0.11, 0.12 nm/V respectively, that is a factor 7–20 smaller. For InSe, Ref. 13 reports 6.39 nm/V at 1.55 eV whereas we find 0.43 nm/V—that is a factor 15 smaller.

Previously, large differences in the experimental estimate of the SHG coefficients—over a range of three orders of magnitude4,5,12 were observed for the MoS$_2$ monolayer. Eventually, Clark and coworkers14 explained that such differences depend on the model assumed to extract the value of the SHG from the experimental data. Indeed, experimentally the SHG is obtained from the measured second-harmonic intensity. Extracting the SHG coefficient is not straightforward and implies to assume a model for the system: Clark and coworkers14 argued that 2D materials should be modelled as a ‘sheet’, as in Refs. 4 and 12, rather than as ‘bulk’, as in Ref. 5. Further, they provide an expression for the difference between $\chi^{(2)}_{\text{sheet}}$ and $\chi^{(2)}_{\text{bulk}}$, i.e. the SHG coefficient estimated either using the ‘sheet’ or the ‘bulk’ model:

$$\frac{\chi^{(2)}_{\text{bulk}}}{\chi^{(2)}_{\text{sheet}}} = 32\pi F \frac{n_{2D}(\omega)\sqrt{n_{2D}(2\omega)}}{(n_{\text{sub}} + 1)^3},$$

where $n_{2D}$ and $n_{\text{sub}}$ are the refractive index for the 2D material and of the substrate, while $F$ is an “overall scaling factor”14.

For MoS$_2$, this ratio can be as large as 9014 and thus accounts for the differences in the experimental estimates.12,13 It also indicates that the ‘bulk’ model leads to too large values for the SHG coefficient. This conclusion is also comforted by accurate theoretical predictions24,46 that reported values close to the experimental estimates that assume the ‘sheet’ model.

Coming back to the monochalcogenides, all the experimental values reported for the GaSe and InSe assumed a bulk model. To investigate whether this is the reason for the discrepancy with the theoretical estimates we use Eq. 2 with: $n_{\text{sub}} \approx 1.45$ (fused silica); $n_{\text{GaSe}}(\omega) = n_{\text{GaSe}}(2\omega) = 2.8$8 and $n_{\text{InSe}}(\omega) = 2.86$ and $n_{\text{InSe}}(2\omega) = 3.35$.13 We obtain ratios as high as $\approx 32$ for GaSe and $\approx 36$ for InSe. Note that we set $F = 1$, rather than its value that is approximately 20, since the experimental estimates already account for various gain/loss factors. These large ratios indicate that, the experimental estimate would be significantly smaller and in sub-
stantial agreement with the theoretical predictions if using the ‘sheet’ model. Residual differences between the experimental and theoretical value could be due to the effects of the substrate and of the surface contributions to the SHG (15,16), which are neglected in the theoretical calculations. Another factor, on the side of the theoretical calculations, could be the chosen dephasing parameter as discussed in Sec. I. The so-corrected experimental estimate for GaSe is as well closer to the SHG coefficients for the bi- and trilayer (15,16) which have been obtained by modeling the few-layers as a bulk medium and accounting for interference in the multilayer system.

In summary, using accurate first-principles real-time simulations based on many-body theory, we confirm strong SHG coefficients. In particular, for InSe we obtain a SHG coefficient of approximately 0.5 nm/V at 1.67 eV—close to maximum gain and laser efficiency of Ti:Sapphire. In substantial agreement with previous theoretical works, we found that the SHG coefficients are not as strong as claimed in the experimental works of Refs. 8 and 13, differing by an order of magnitude. We argue that the experimental values are overestimated due to the assumption of a ‘bulk’ rather than a more appropriate ‘sheet’ model to extract the SHG from the measurements and they need to be reviewed. We have shown indeed that a substantial agreement between theoretical and experimental values is recovered when a ‘sheet’ model is used to extract the SHG from the experimental data.

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